Local defects and ferrom agnetism in graphene layers.

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W e study the changes in the electronic structure induced by lattice defects in graphene planes. In m any cases, lattice distortions give rise to localized states at the Ferm i level. E lectron-electron interactions lead to the existence of local m om ents. The RKKY interaction between these m om ents is always ferrom agnetic, due to the sem in etallic properties of graphene.

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Introduction. A number of recent experiments suggest that pure graphite behaves as a highly correlated electron system [1]. In particular it shows a metalinsulator transition in magnetic elds and insulating behavior in the direction perpendicular to the planes in dierent sam ples [1, 2, 3, 4, 5, 6, 7, 8]. Recent results show ferrom agnetic behavior[9], enhanced by proton bom bardm ent [10], what opens up a new way to the creation of organic magnets[11]. In this paper we study the formation of local moments near simple defects. It is shown that m any types of lattice distortions, like cracks and vacancies, can induce localized states at the Fermi level, leading to the existence of local moments. The RKKY interaction between these moments is always ferrom agnetic due to the sem in etallic properties of graphite. Hence, the RKKY interaction does not lead to frustration and spin glass features.

The model. The conduction band of graphite is well described by a tight binding model which includes the orbitals which are perpendicular to the graphite planes at each C atom [12]. If the interplane hopping is neglected, this model describes a sem in etal, with zero density of states at the Ferm i energy, and where the Ferm i surface is reduced to two inequivalent K -points located at the corner of the hexagonal B rillouin Zone. The low -energy excitations with momenta in the vicinity of the Ferm i points have a linear dispersion and can be described by a continuum model which reduces to the D irac equation in two dimensions[12, 13, 14, 15, 16]. The Ham iltonian density of the system is

z syste Z

$$H_0 = hv_F \quad d^2r (r) (i_x Q_x + i_y Q_y) (r);$$
 (1)

where the components of the two-dimensional spinor $(x) = (_1(x);_2(x))$ correspond to the Bloch states of the two sublattices in the honeycomb structure, independent in the absence of interactions. In the clean two-dimensional system there is no room for low energy electronic instabilities, the short range interactions being inrelevant due to the vanishing density of states at the Ferm i level.

It is known that disorder signi cantly changes the states described by the two dimensional Dirac equation [17, 18, 19], and, usually, the density of states at low energies is increased. Lattice defects, such as pentagons and heptagons, or dislocations, can be included in the continuum model by means of a non-abelian gauge ekl[14, 20] that reproduces the e ects of the curvature of the lattice and the possible exchange of Ferm i points. W ithin the same theoretical scheme it has also been shown that certain types of disorder random ly distributed in the graphene lattice enhances the e ect of the interactions[21] and can stabilize new phases. In addition, a graphene plane can show states localized at interfaces[22, 23], which, in the absence of other types of disorder lie at the Ferm i energy. Structures with m ixed sp² and sp³ bonding can also lead to localized states[24].

The tight binding model de ned by the orbitals at the lattice sites can have edge states when the sites at the edge belong all to the same sublattice [22, 23, 25] (zigzag edge). These states lie at zero energy which for neutral graphene planes correspond to the Ferm i energy. In the continuum model described earlier localized states are norm alizable solutions $(_1(\mathbf{r});_2(\mathbf{r}))$ of the D irac equation:

$$(\theta_{x} + i\theta_{y})_{1}(x) = 0$$

 $(\theta_{x} i\theta_{y})_{2}(x) = 0$ (2)

These equations are satisfied if $_1(\mathbf{r})$ is an analytic function of z = x + iy and $_2(\mathbf{r}) = 0$, or if $_1(\mathbf{r}) = 0$ and $_2(\mathbf{r})$ is an analytic function of z = x iy. Zigzag edge states can be obtained as follows. Consider a sem i-in nite honeycom b lattice with an edge at y = 0 and which occupies the half plane x > 0. A possible solution which decays as $x \mid 1$ is

$$_{1}(x;y) / e^{kz} = e^{iky}e^{kx}; _{2}(x) = 0:$$

These solutions satisfy the boundary conditions at y = 0 if the last column of carbon atoms belong to the sublattice where the component $_1$ is dened. Then, the next column belongs to the other sublattice, where the amplitude of the state is, by construction, zero.

This kind of solutions can be generalized to describe other types of extended defects that will be produced in experiments where graphite sam ples are bom barded by protons. In a strongly disordered sam ple, large defects

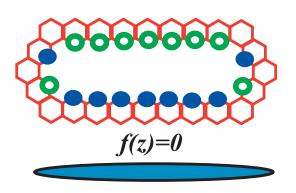


FIG. 1: E longated crack in the honeycomb structure. The crack is such that the sites in the upper edge belong to one sublattice, while those at the lower edge belong to the other. Bottom : approximate cut in the complex plane which can be used to represent this crack at long distances.

m ade up of m any vacancies can exist. These defects will give rise to localized states, when the term ination at the edges is locally sim ilar to the surfaces discussed above. Note that, if the bonds at the edges are saturated by bonding to other elements, like hydrogen, the states at these sites are removed from the Ferm ienergy, but a sim – ilarboundary problem arises for the remaining orbitals. The only possible localized states can exist at zero energy, where the density of extended states vanishes. The wave functions obtained from the D irac equations will be norm alizable and analytic functions of the variables z = x + iy or z = x iy of the form

(z) [f(z);0]

obeying the boundary conditions in posed by the shape of the defect.

Extended vacancies with approximate circular shape can support solutions of the type

$$f(z) / z^{n}; n > 1$$
:

By using conform alm apping techniques, solutions can be found with the boundary conditions appropriate to the shapes of di erent defects.

A simple case is the elongated crack depicted in Fig.[1], which we assume to extend from x = a to x = a, and to have a width comparable to the lattice constant along the y axis. The analytic function f(z) associated with localized states near a crack of this shape should satisfy R ef (z) = 0 at the crack edges, because the boundaries of the crack include atom s from the two sublattices. Hence, the boundary of the crack leads to a branch cut in the com plex function f(z). Labelling edge states by a quantum num bern, we nd that the function can be written for these states as:

n Re
$$\frac{A}{z^n \overline{z^2 a^2}}$$
;0 :

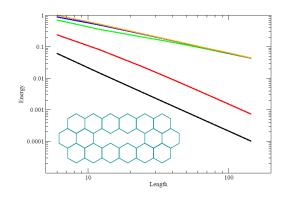


FIG.2: Energy of the ve states with positive energy closest to = 0 for a cluster of size L L which contains at the center the defect shown in the inset. Periodic boundary conditions are used. The spectrum is symmetric around = 0.

A similar solution is obtained by exchanging the upper by the lower spinor component, and replacing $z \ z$. Because of the discreteness of the lattice, the allowed values of n should be smaller than the number of lattice units spanned by the crack.

We have checked numerically the existence of these localized states by diagonalizing the tight binding ham iltonian in nite lattices of di erent sizes. The dependence of some of the states close to the chemical potential (zero energy) on the cluster size is shown in Fig.[2]. The delocalized states show a dependence $_{del} / L^{-1}$, consistent with the properties of the D irac equation from which they can be derived. The states closest to = 0, show a dependence $_{loc} / L^{-2}$, which suggest a power law localization, in agreem ent with the previous analysis.

These states are half led in a neutral graphene plane. In the absence of electron interactions, this leads to a large degeneracy in the ground state. A nite local repulsion will tend to induce a ferrom agnetic alignm ent of the electrons occupying these states, as in sim ilar cases with degenerate bands[26].

To verify this behavior and to com pare with previous results we have perform ed an unrestricted H artree Fock calculation of the graphene cluster with di erent types of defects including large vacancies as the one shown in Fig.[1]. Sim ilar calculations done in graphene ribbons have shown non-bonding molecular orbitals localized m ainly along the zigzag edges (edge states) [27, 28]. These edges have partly at bands which give rise to a sharp peak in the density of states at the Ferm ienergy. A nite on-site C oulom b interaction leads to an instability of these at bands and to the existence of spin-polarized states. We have veri ed that the sim ilar behavior can

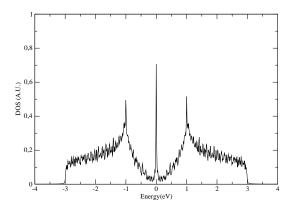


FIG. 3: Density of states of a 26 26 cluster with a large defect with zig-zag boundary as the one shown in Fig.[1] The on-site interaction term is U = 0.

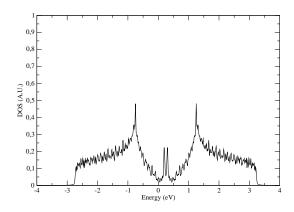


FIG.4: Same as Fig.[3] with an on-site interaction U = 0.5t.

also be obtained near the boundary of a large defect as the one shown in Fig.[1]. We have perform ed calculations in a honeycomb lattice of various sizes with a maximum of 26 26 unit cells, i. e. a cluster of 52 52 sites. In the absence of defects the density of states is zero at the Ferm i level. Figure β] shows the charge density distribution of a lattice with an extended vacancy shaped as shown in Fig.[1], without on-site interaction. The Ferm i level is located at zero. A peak in the Ferm i level is form ed due to the presence of the defect. The totalm agnetization of the cluster is zero. When the on-site interaction is switched on, a spin polarization arises of a m agnitude proportional to the size of the defect. Fig.[4] shows the density pro le of the polarized cluster obtained with U = 0.5t.

N ext we will analyze the in uence of these magnetic m om ents on the conduction band. The hopping between the states involved in the form ation of these m om ents and the delocalized states in the conduction band vanishes by de nition, if the localized states lie at zero energy. Hence, a K ondo-like coupling m ediated by the hopping will not be induced. The localized electrons act as a reservoir of localized m om ents, which interact with the valence electrons via the on site Hubbard repulsion, U. The wavefunction of the localized electrons overlaps on m any sites with the valence electrons. On these sites, the valence electrons will tend to be polarized with their spins parallel to the spins of the localized electrons. The change in the energy at a given site for the valence electrons near the defect is of order U, distributed over N sites. Then, the valence electrons will induce long range RKKY interactions between the localized m om ents, which can be estim ated by adding the contributions from all sites. W e nd:

$$\frac{Z}{J_{RKKY}(t)} = U^{2}N^{2} d^{2}ke^{ikt}(k) = U^{2}N^{2}\frac{a^{4}}{v_{F}jt^{2}}$$
(3)

W here a is the lattice constant, and the static susceptibility is given by: (\tilde{K}) / \tilde{K} j[16], and a is the lattice constant.

D ue to the absence of a nite Ferm isurface, the RKKY interaction in eq.(3) does not have oscillations. Hence, there are no competing ferro-and antiferrom agnetic couplings, and the magnetic moments will tend to be ferrom agnetically aligned. The total polarization per unit area at low temperatures is proportional to N c, where c is the concentration of defects, and N is proportional to the average size.

We can make an estimate of the Curie temperature from the coupling between the local magnetic moments given in eq.(3). The entropy cost of aligning ferrom agnetically moments is S T per moment. The average distance between moments is jrj c¹⁼². Hence, the free energy per moment in the ferrom agnetic phase can be written as:

F (m) =
$$c_1 \frac{U^2 N^2 a^4 c^{3=2}}{v_F} + c_2 T m^2 + (4)$$

where c_1 and c_2 are num erical constants of order unity. The value of the free energy will be negative (and below the value in the param agnetic phase) at a Curie tem perature given by:

$$T_{c} = \frac{U^{2}N^{2}a^{4}c^{3=2}}{v_{F}} = \frac{U^{2}}{W}\frac{Na^{3}}{L^{3}}$$
(5)

where W is the conduction electron bandwidth, $W = v_F = a$, and l is the average distance between in purities.

The Curie tem perature depends on the concentration and size of the defects. A ssum ing, as an example, that 10 and 1 10^2 a, we obtain a saturation m agnetiza-Ν tion of 10³ Bohrm agnetons per unit cell, and a Curie 10 ${}^{4}\text{U}{}^{2}=W$. The value of U ${}^{2}=W$ can tem parature T_C be estimated to be 1eV. Then, these arguments give 1K. This tem perature is considerably lower than T_{C} the experimentally observed ones. It is worth noting, however, that this analysis does not take into account the enhancement of the susceptibility of the conduction electrons, percolation e ects due to the random distribution of in purities, and the nite extension of the localized states induced by the defects.

Conclusions. We have shown that, under very general circum stances, lattice defects, vacancies and voids in the graphene structure give rise to localized states at the Ferm i energy. The number of these states scales roughly with the perimeter of the defect. Repulsive electron-electron interactions lead to the polarization of these states, and to the form ation of localm oments. The RKKY interaction mediated by the valence electrons decays as r^3 , where r is the distance between defects, and shows no oscillations, due to the vanishing of the Ferm i surface in a graphene layer. The interaction is ferror agnetic, and the system cannot show the fustration e ects and spin glass features observed in other disordered sys-

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tem s with localm om ents. On the other hand, the Curie tem perature estimated assuming a random distribution of localm om ents is low, $T_{\rm C}$ $\,$ 1K, for reasonable values of the defect concentration. It may happen that percolation e ects, and the nite extension of the localized states which give rise to the localm om ents will increase the value of $T_{\rm C}$.

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